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Vishay Semiconductors

RoHS

COMPLIANT

Phase Control Thyristor RMS SCRs, 25 A, 35 A



| TO-48 (| TO-208AA) |
|---------|-----------|
|---------|-----------|

| PRIMARY CHARACTERISTICS | | | | | |
|------------------------------------|---|--|--|--|--|
| I _{T(AV)} | 16 A, 22 A | | | | |
| I _{T(RMS)} | 25 A, 35 A | | | | |
| V _{DRM} /V _{RRM} | 25 V, 50 V, 100 V, 150 V, 200 V, 250 V, 300 V, 400 V, 500 V, 600 V, 700 V, 800 V, 1000 V 1200 V | | | | |
| V _{TM} | 2.3 V | | | | |
| I _{GT} | 60 mA | | | | |
| TJ | -40 °C to +125 °C | | | | |
| Package | TO-48 (TO-208AA) | | | | |
| Circuit configuration | Single SCR | | | | |

FEATURES

- General purpose stud mounted
- Broad forward and reverse voltage range through 1200 V
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

| MAJOR RATINGS AND CHARACTERISTICS | | | | | | |
|-----------------------------------|-----------------|----------------------------|----------------------------|------------------|--|--|
| PARAMETER | TEST CONDITIONS | VALUES 2N681-92 | VALUES 2N5205-07 | UNITS | | |
| 1 | | 16 ⁽¹⁾ | 22 (1) | А | | |
| I _{T(AV)} | T _C | -65 to +65 ⁽¹⁾ | -40 to +40 | °C | | |
| I _{T(RMS)} | | 25 | 35 | А | | |
| 1 | 50 Hz | 145 | 285 | ۸ | | |
| I _{TSM} | 60 Hz | 150 ⁽¹⁾ | 300 (1) | A | | |
| l ² t | 50 Hz | 103 | 410 | A ² s | | |
| 141 | 60 Hz | 94 | 375 | A-S | | |
| I _{GT} | | 40 | 40 | mA | | |
| dV/dt | | - | 100 (1) | V/µs | | |
| dl/dt | | 75 to 100 | 100 | A/µs | | |
| V _{DRM} | Range | 25 to 800 | 600 to 1200 | V | | |
| V _{RRM} | Range | 25 to 800 | 600 to 1200 | V | | |
| TJ | | -65 to +125 ⁽¹⁾ | -40 to +125 ⁽¹⁾ | °C | | |

Note

(1) JEDEC[®] registered value

VS-2N681, VS-2N5205 Series



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ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS (APPLIED GATE VOLTAGE ZERO OR NEGATIVE) | | | | | | | |
|---|--|--|-------------------|--|--|--|--|
| TYPE NUMBER | V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND OFF-STATE VOLTAGE V | V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE (t _p < 5 ms) V | Тј | | | | |
| VS-2N681 | 25 | 35 | | | | | |
| VS-2N682 | 50 | 75 | | | | | |
| VS-2N683 | 100 | 150 | | | | | |
| VS-2N684 | 150 | 200 | | | | | |
| VS-2N685 | 200 | 300 | | | | | |
| VS-2N686 | 250 | 350 | | | | | |
| VS-2N687 | 300 | 400 | -65 °C to +125 °C | | | | |
| VS-2N688 | 400 | 500 | | | | | |
| VS-2N689 | 500 | 600 | | | | | |
| VS-2N690 | 600 | 720 | | | | | |
| VS-2N691 | 700 | 840 | | | | | |
| VS-2N692 | 800 | 960 |] | | | | |
| VS-2N5205 | 800 | 960 | | | | | |
| VS-2N5206 | 1000 | 1200 | -40 °C to +125 °C | | | | |
| VS-2N5207 | 1200 | 1440 | 1 | | | | |

Note

• JEDEC registered values

| PARAMETER | SYMBOL | TEST CON | DITIONS | VALUES 2N681-92 | VALUES 2N5205-07 | UNITS |
|---|---------------------|--|---|---------------------------------|---------------------------|------------------|
| Maximum average on-state | | 100° half aine wave good | ation | 16 ⁽¹⁾ | 22 ⁽¹⁾ | Α |
| current at case temperature | I _{T(AV)} | 180° half sine wave condu | CLION | -65 to +65 ⁽¹⁾ | -40 to +40 ⁽¹⁾ | °C |
| Maximum RMS on-state current | I _{T(RMS)} | | | 25 | 35 | А |
| | | 50 Hz half cycle sine wave or 6 ms rectangular pulse | Following any rated load condition, and | 145 | 285 | |
| Maximum peak, one-cycle non-repetitive surge current | | 60 Hz half cycle sine wave or 5 ms rectangular pulse | - | 150 ⁽¹⁾ | 300 (1) | |
| | I _{TSM} | 50 Hz half cycle sine wave Same conditions a or 6 ms rectangular pulse above except with | | 170 | 340 | A |
| | | 60 Hz half cycle sine wave or 5 ms rectangular pulse | V _{RRM} applied following surge = 0 | 180 | 355 | |
| | | t = 10 ms Rated V _{BRM} applied | | 103 | 410 | |
| Maximum I ² t capability for fusing | l ² t | t = 8.3 ms | following surge, initial T _J = 125 °C | 94 | 375 | A ² s |
| Maximum I ² t capability for | | t = 10 ms | V _{RRM} = 0 following | 145 | 580 | |
| individual device fusing | | t = 8.3 ms surge, initial T_J = 125 °C | | 135 | 530 | |
| Maximum I ² \t capability for individual device fusing | l²√t (2) | t = 0.1 ms to 10 ms, initial $T_J < 125 \text{ °C}$ V _{RRM} applied following surge = 0 | | 1450 | 5800 | A²√s |
| Maximum peak on-state voltage | V _{TM} | $T_J = 25 \text{ °C}, I_{T(AV)} = 16 \text{ A} (50)$ $I_{T(AV)} = 22 \text{ A} (70 \text{ A peak}) 2 \text{ N}$ | 2 (1) | 2.3 ⁽¹⁾ | v | |
| Maximum holding current | I _H | Anode supply 24 V, initial I | 20 at 25 °C (typical) | 200 ⁽¹⁾ at -40 °C | mA | |

Notes

⁽¹⁾ JEDEC registered value

⁽²⁾ I²t for time $t_x = I^2 \sqrt{t} \cdot \sqrt{t_x}$

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VS-2N681, VS-2N5205 Series

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| SWITCHING | | | | | |
|-----------|----|-----|----|----|---|
| | GV | VIT | СЦ | IN | 2 |

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| SWITCHING | | | | | | |
|--|----------------------------------|----------------|---|--------------------|---------------------|-------|
| PARAME | TER | SYMBOL | TEST CONDITIONS | VALUES 2N681-92 | VALUES 2N5205-07 | UNITS |
| | V _{DM} = 25 V to 600 V | | $T_C = 125 \text{ °C}, V_{DM} = \text{Rated } V_{DRM},$ | 100 | - | |
| Maximum non-repetitive rate of rise of turned-on | V _{DM} = 700 V to 800 V | dl/dt | $I_{TM} = 2 \times dI/dt$, gate pulse = 20 V, 15 Ω , $t_p = 6 \mu s$, $t_r = 0.1 \mu s$ maximum Per JEDEC standard RS-397, 5.2.2.6 | 75 | - | A∕µs |
| current | | ai/at - | $ \begin{array}{l} T_{C} = 125 \ ^{\circ}\text{C}, \ V_{DM} = 600 \ V, \ I_{TM} = 200 \ A \ at \\ 400 \ Hz \ maximum, \ gate \ pulse = 20 \ V, \ 15 \ \Omega, \\ t_{p} = 6 \ \mu s, \ t_{r} = 0.1 \ \mu s \ maximum \\ \text{Per JEDEC standard RS-397, } 5.2.2.6 \end{array} $ | - | 100 | 7 μ3 |
| Typical delay time | | t _d | $\label{eq:T_C} \begin{array}{l} T_{C} = 25 \ ^{\circ}\text{C}, \ V_{DM} = \text{Rated} \ V_{DRM}, \ I_{TM} = 10 \ \text{A} \\ \text{DC resistive circuit, gate pulse} = 10 \ \text{V}, \\ 40 \ \Omega \ \text{source,} \ t_{p} = 6 \ \mu\text{s}, \ t_{r} = 0.1 \ \mu\text{s} \end{array}$ | 1 | 1 | μs |

BLOCKING

| PAR | AMETER | SYMBOL | TEST CONDITIO | NS | VALUES 2N681-92 | VALUES 2N5205-07 | UNITS |
|--|--|--------------------|---|-----------|--------------------|---------------------|-------|
| Minimum critical rate | of | dV/dt | T _J = 125 °C, exponential to 100 % rated V _{DRM} | Gate open | 100 (typical) | 100 (1) | V/µs |
| rise of off-state voltag | ge | uv/ui | $T_J = 125 \text{ °C}$, exponential to 67 % rated V_{DRM} | circuited | 250 (typical) | 250 | v/µs |
| | V_{RRM} , V_{DRM} = 400 V | | | | 3.5 | - | |
| | V_{RRM} , V_{DRM} = 500 V | | | | 3.5 | - | |
| Ma. 1 | V_{RRM} , V_{DRM} = 600 V | I _{DRM} , | | | 2.5 | 3.3 | |
| Maximum reverse leakage current | V _{RRM} , V _{DRM} = 700 V | | T _J = 125 °C | | 2.2 | - | mA |
| $\frac{V_{\text{RRM}}, V_{\text{DRM}} = 800 \text{ V}}{V_{\text{RRM}}, V_{\text{DRM}} = 1000 \text{ V}}$ | I _{RRM} | | | 2 | 2.5 | | |
| | V _{RRM} , V _{DRM} = 1000 V | | | | - | 2 |] |
| | V _{RRM} , V _{DRM} = 1200 V | | | | - | 1.7 | 1 |

Note

⁽¹⁾ JEDEC registered value

| PARAMETER | SYMBOL | | TEST CONDITIONS | VALUES | VALUES | UNITS |
|---|--------------------|--------------------------------------|--|---------------------|---------------------|-------|
| FANAMETEN | STWDUL | | TEST CONDITIONS | 2N681-92 | 2N5205-07 | UNITS |
| Maximum peak gate power | P_{GM} | | 2N681 series; or 2N5204 series | 5 (1) | 60 ⁽¹⁾ | w |
| Maximum average gate power | P _{G(AV)} | | | 0.5 ⁽¹⁾ | 0.5 ⁽¹⁾ | |
| Maximum peak positive gate current | +I _{GM} | | | 2 (1) | 2 | Α |
| Maximum peak positive gate voltage | +V _{GM} | | | 10 ⁽¹⁾ | - | v |
| Maximum peak negative gate voltage | -V _{GM} | | | 5 (1) | 5 (1) | v |
| Maximum required DC gate | | T _C = min. rated value | Maximum required gate trigger current is the lowest value which will trigger all units with + 6 V anode to cathode | 80 (1) | 80 (1) | |
| current to trigger | I _{GT} | T _C = 25 °C | | 40 | 40 | mA |
| | | T _C = 125 °C | | 18.5 | 20 | |
| Typical DC gate current to trigger | | T _C = 25 °C, + | 6 V anode to cathode | 30 | 30 | |
| Maximum required DC gate voltage to trigger | V _{GT} | T _C = -65 °C | Maximum required gate trigger voltage is the lowest value which will trigger all units with + 6 V anode to cathode | 3 (1) | 3 (1) | v |
| | | T _C = 25 °C | | 2 | 2 | |
| Typical DC gate voltage to trigger | | T _C = 25 °C, + | 6 V anode to cathode | 1.5 | 1.5 | |
| Maximum DC gate voltage not to trigger | V _{GD} | T _C = 125 °C | Maximum gate voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode | 0.25 ⁽¹⁾ | 0.25 ⁽¹⁾ | v |

Note

⁽¹⁾ JEDEC registered value

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VS-2N681, VS-2N5205 Series

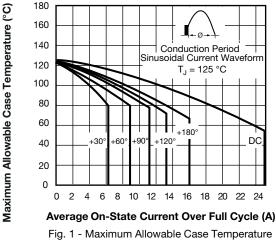


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| THERMAL AND | THERMAL AND MECHANICAL SPECIFICATIONS | | | | | | | | | |
|---|---------------------------------------|-----------------------------------|--|---------------------------|---------------------------|----------|--|--|--|--|
| PARAMETER | | SYMBOL TEST CONDITIONS | | VALUES 2N681-92 | VALUES 2N5205-07 | UNITS | | | | |
| Operating junction and storage temperature rar | nge | T _J , T _{Stg} | | -65 to 125 ⁽¹⁾ | -40 to 125 ⁽¹⁾ | °C | | | | |
| Maximum internal therm junction to case | al resistance, | R _{thJC} | DC operation | 1.5 | 1.5 ⁽¹⁾ | °C/W | | | | |
| Typical thermal resistan case to sink | ce, | R _{thCS} | Mounting surface, smooth, flat and greased | 0.35 | 0.35 | 0/10 | | | | |
| to nut Mounting torque ± 10 % to device | | | L. I. Sector data sector | 20 (27.5) | | lbf · in | | | | |
| | | | Lubricated threads (Non-lubricated threads) | 0.23 (0.32) | | kgf∙cm | | | | |
| | | | (Non-lubicated threads) | | 2.3 (3.1) | | | | | |
| | | | | | 25 | | | | | |
| | | Lubricated threads | | 0.29 | | kgf · cm | | | | |
| | | | | 2.8 | | N·m | | | | |
| Approximate weight | | | | 14 | 14 | g | | | | |
| | | | | 0.49 | 0.5 | oz. | | | | |
| Case style | | | | TO | -48 (TO-208AA) | | | | | |

Note

⁽¹⁾ JEDEC registered value



vs. Average On-State Current, 2N681 Series

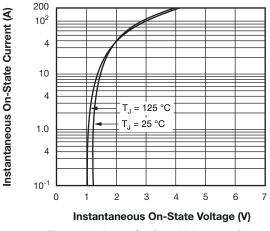
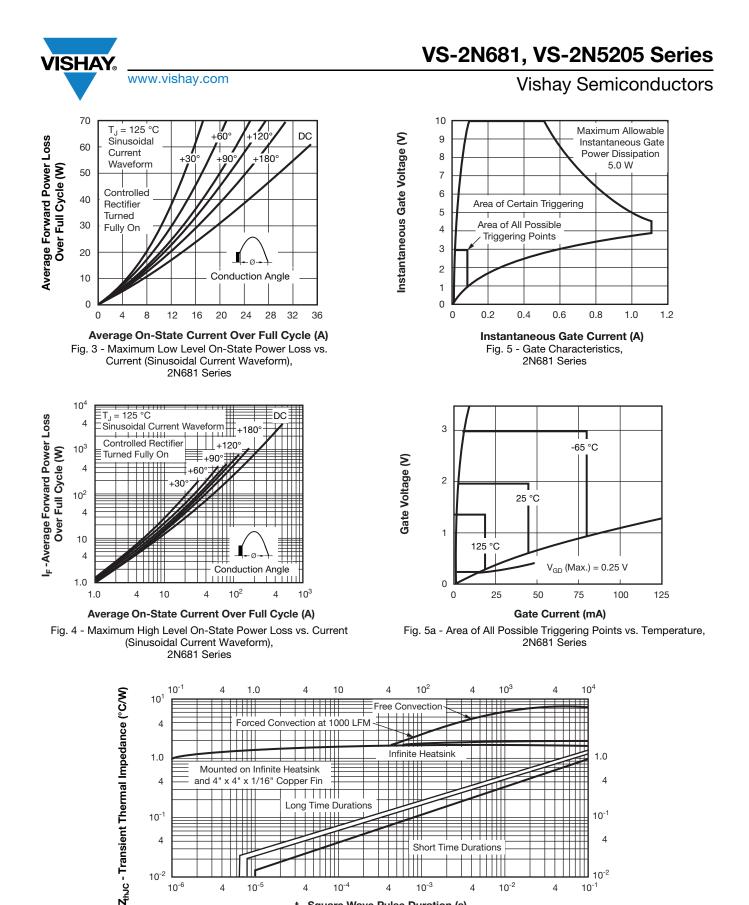
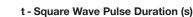
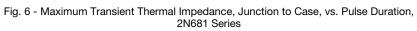
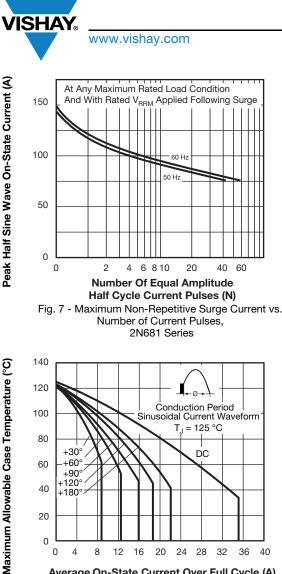


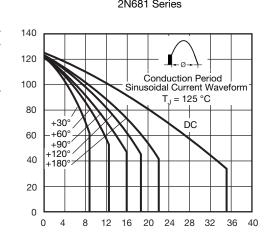
Fig. 2 - Maximum On-State Voltage vs. Current, 2N681 Series











Average On-State Current Over Full Cycle (A) Fig. 8 - Maximum Allowable Case Temperature vs. Average

On-State Current (Sinusoidal Current Waveform), 2N5205 Series

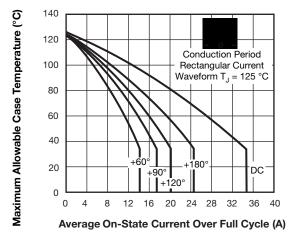


Fig. 9 - Maximum Allowable Case Temperature vs. Average On-State Current (Rectangular Current Waveform), 2N5205 Series

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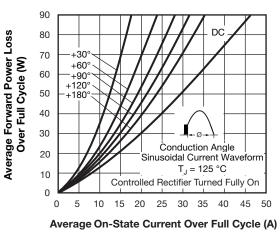


Fig. 10 - Maximum Low-Level On-State Power Loss vs. Average On-State Current (Sinusoidal Current Waveform), 2N5205 Series

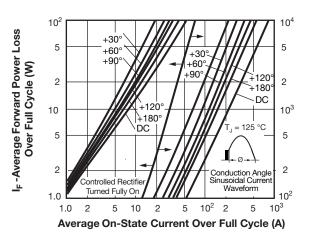
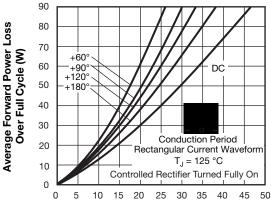


Fig. 11 - Maximum High-Level On-State Power Loss vs. Average On-State Current (Sinusoidal Current Waveform), 2N5205 Series



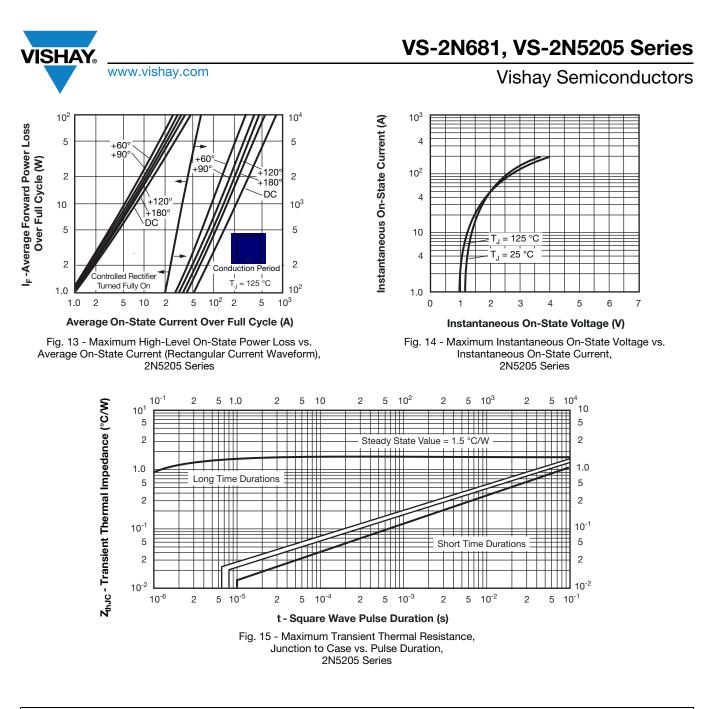
Average On-State Current Over Full Cycle (A)

Fig. 12 - Maximum Low-Level On-State Power Loss vs. Average On-State Current (Rectangular Current Waveform), 2N5205 Series

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